Comparative Study of Diamond Films Grown on Silicon Substrate
Using Microwave Plasma Chemical Vapor Deposition
and Hot-Filament Chemical Vapor Deposition Technique

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Abstract—Diamond films on the p-type Si(111) and p-type(100) substrates were prepared by microwave plasma chemical vapor deposition (MWCVD) and hot-filament chemical vapor deposition (HFCVD) by using a mixture of methane CH$_4$ and hydrogen H$_2$ as gas feed. The structure and composition of the films have been investigated by X-ray Diffraction, Raman Spectroscopy and Scanning Electron Microscopy methods. A high quality diamond crystalline structure of the obtained films by using HFCVD method was confirmed by clear XRD-pattern: SEM images show that the prepared films are polycrystalline diamond films consisting of diamond single crystallites (111)-orientation perpendicular to the substrate. Diamond films grown on silicon substrates by using HFCVD show good quality diamond and fewer non-diamond component.

Key words: Diamond, HFCVD, MWCVD

INTRODUCTION

Diamond is one of the most important materials for advanced engineering due to its unique and extreme properties in hardness, wear resistance, good thermal expansion coefficient and room temperature thermal conductivity of any known material as well as low coefficient of friction. Applications include coatings for machine cutting tools, heat sinks for electronic devices and protective coatings for aerospace component. Diamond can be synthesized by various methods [Alder and Christian, 1961; Bundy, 1963; Choi et al., 1994; Kanda et al., 1994; Lux et al., 1992; Stepban et al., 1992; Yim et al., 2001]. Unfortunately, due to the high cost, limited size, and uneasily controlled impurities of natural and synthetic high-pressure, high-temperature (HPHT) diamond, the diamond applications have in fact been limited in comparison to its great potential. CVD diamond can overcome these difficulties, and is the most promising avenue available for synthetic diamond [Shendorova et al., 2002]. The major CVD diamond-techniques are the hot-filament, arcjet-torch, AC- and DC-discharge, radio-frequency plasma, and microwave plasma methods. Carbon is unique in that simple changes in its local bonding can give rise to materials as diverse as diamond, graphite, fullerene, carbon nanotubes, and disordered, nanostuctured and amorphous carbon [Shendorova et al., 2002]. That is why diamond nucleation and growth, particularly on non-diamond substrates, is an issue of current interest for growing diamond films for electronic and optical applications. In a previous study, we reported the growth of Lonsdaleite diamond on flashed and reconstructed Si(100) and the nucleation of diamond on carbon nanotubes as a seed

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layer by HFCVD [Ansari et al., 2004; Cheim et al., 2003]. In this communication, we study the diamond grown films on silicon substrate by using HFCVD and MWCVD. A mixture of CH$_4$/H$_2$ was used as the feed gas. The film structure and composition were characterized by SEM, XRD and Raman methods.

EXPERIMENTAL

1. Microwave Chemical Vapor Deposition (MWCVD)

The diamond depositions were conducted in a 2.45-GHz Applied Science Technology (ASTec), USA, made AX-2115 system with a stainless-steel vacuum chamber of cylindrical shape of 18 cm diameter and 30 cm high, as presented schematically in Fig. 1(a).

Silicon wafers (111) orientation was used as substrates. In order to diamond nucleation enhancement, Si-substrates were scratched by diamond powder of up to 10 µm size. After loading Si-substrate into vacuum chamber, it was evacuated to a base pressure of <10$^{-6}$ torr by the high vacuum system. Then a mixture of 3 scm (standard cubic centimeter per minute) of 99.999 pure methane CH$_4$ and 300 scm of 99.999 pure hydrogen H$_2$ is inlet into chamber by gas system; gas flow rates were controlled by MFC (mass flow controller) with a precision of 0.1 sccm and 1.0 sccm for methane and hydrogen, respectively. Total pressure in the chamber was kept at 50 torr=1 torr during deposition time. Base substrate temperature T$_{\text{sub}}$ with accuracy ±1 °C was measured by thermocouple and controlled by substrate heater and surface substrate temperature T$_{\text{surf}}$ was measured by optical pyrometer. Two series of samples have been deposited under conditions summarized in Table 1.

2. Hot-Filament Chemical Vapor Deposition (HFCVD)

All experiments were carried out on p-Si(100) substrates scratched manually by using diamond paste with 1 µm particles. The particles
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were washed with acetone and de-ionized water. The system was evacuated to a base pressure ~10^{-9} torr. Tungsten filament was positioned at a 5 mm distance from the substrate, as presented schematically in Fig. 1(b) and heated to 2,150 ± 50 °C as measured using an optical pyrometer Minolta TR-630, Japan. A gas mixture of H\textsubscript{2} (99.999\%) and CH\textsubscript{4} (99.5\%) in 1 : 100 proportions was introduced in the deposition chamber at a flow rate of 100 sccm, so that the pressure inside the chamber rose to 30 ± 2 torr. Deposition was carried out for two hours.

X-ray diffractometry (XRD), scanning electron microscopy (SEM), and Raman spectroscopy were used for film investigations.

RESULTS AND DISCUSSION

Surface morphology: Typical SEM images of diamond film on scratched Si(111) and Si(100) by using Microwave chemical vapor deposition (HWCVD) and hot-filament chemical vapor deposition (HFCVD) techniques are illustrated in Fig. 2. It is clear from (a) that the film was composed from particles of different size from nano- to micro-scale. Here the grown film impression is that the particles are larger and a carefully examination of sample (b) shows that there are many triangular platelets on top of bigger crystals. These triangles have sides ~1.5 µm in length and they are (111) oriented crystallites. This type of surface morphology is typical for diamond (111)-directions growth [Stammle et al., 2002]. These facts indicate that the nucleation and growth processes really continuously occurred during deposition time.

The crystalline structure of the films was characterized by XRD and the patterns are presented in Fig. 3. In both types of sample, a peak at the Bragg angle of ~43.9° is observed indicating the diffraction from (111)-plane. This peak corresponds to typical cubic diamond peak as can be seen in the JCPDS cards (06-0675).

Diamond grown films were also analyzed by micro Raman spectroscopic technique. Raman scattering is very powerful means for characterization of carbon-bonding [Ferrari, 2002]. Carbyne has no crystalline structure and gives Raman peaks at a wavenumber ~2,100 cm^{-1} [Ferrari et al., 2003]. Graphite has crystalline structure \( A_{\text{r}} \) type, characterized by flat hexagonal layer of covalent sp\(^2\)-bonded...
carbon atoms and van der Waals force between the layers. It depends on the degree of graphitic ordering and there must exist two bands near ~1,580 cm\(^{-1}\) and 1,355 cm\(^{-1}\) in the Raman spectrum called G-band (Graphite) and D-band (Disordered graphitic rings in the flat hexagonal layers) [Ferrari, 2002]. Diamond has crystalline structure A\(_4\)-type, characterized by tetrahedral sp\(^3\)-bonded carbon; and a typical Raman peak of natural crystalline diamond is located at ~1,332 cm\(^{-1}\). For CVD diamond, commonly composed from separate crystallites, there may be observed Raman peaks at ~1,060 cm\(^{-1}\), 1,150 cm\(^{-1}\), 1,260 cm\(^{-1}\), and 1,475 cm\(^{-1}\) due to short-range of diamond ordering (nanodiamond) [Ferrari and Robertson, 2001; Petrov et al., 1999]. The Fig. 4 presents typical Raman spectra for the two types of samples prepared. Raman shows no peak at ~2,100 cm\(^{-1}\) and that confirms no carbyne (sp\(^1\)-hybridization) in the films. Fig. 4(a) shows very sharp and strong peak with FWHM at ~9 cm\(^{-1}\) and at ~1,334.47 cm\(^{-1}\), that is a typical cubic diamond peak. The observed small peaks at ~1,064 cm\(^{-1}\), 1,135 cm\(^{-1}\), 1,255 cm\(^{-1}\) obviously are due to nanodiamond. The large and broad peak at ~1,503 cm\(^{-1}\) is due to a mixture of sp\(^2\)- and sp\(^3\)-carbon, called diamond-like carbon (DLC) [Ferrari and Robertson, 2001]. The nature of small peaks which often appeared at near ~1,373 cm\(^{-1}\), ~1,429 cm\(^{-1}\), and ~1,455 cm\(^{-1}\) like shown in Fig. 4(a) is still questionable. A peak at ~1,447 cm\(^{-1}\) was reported to be for nanodiamond [Petrov et al., 1999]. We suggest that these peaks are due to metastable states because they are not always appearing and their locations are not fixed, but a little bit changed. The other opinion for these peaks can be due to the mixture of disordered tetrahedral sp\(^3\)-carbon presented at the grain boundaries with small portion sp\(^2\)-carbon (for DLC: sp\(^3\)/ sp\(^2\)~30%/60%) or hydrogen generated tetrahedral sp\(^3\)-C:H. For the first situation, the mixture can be identified as defected (or nano-) diamond. The Raman spectrum of the film grown by HFCVD technique (Fig. 4(b) is similar to the well reported spectra with a sharp peak at ~1,333 cm\(^{-1}\) which is a typical diamond peak and a broad peak corresponding to graphitic phase at 1,606 cm\(^{-1}\).

**CONCLUSION**

A comparative study of the growth of polycrystalline film on Si-substrate was carried out by using hot filament chemical deposition (HFCVD) and microwave plasma chemical vapor deposition.
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It was found that films prepared by HFCVD are better in quality than MWCVD prepared films. SEM and Raman spectra indicate that the obtained film should be composed of diamond crystallites A4-type cubic structure ranging from nano- to micro-scale. Raman spectra also confirm that the prepared films consist mostly of sp3-bonded carbon in the diamond structure, and only a small portion of sp2-bonded carbon coexists together with sp3-carbon in the thin boundaries between diamond crystallites. There is no sp2-bonded carbon in the graphic ordering in the prepared film.

ACKNOWLEDGMENT

M. A. Dar acknowledges the KOSEF graduate student fellowship program. This work was supported by KMOST (2004-01352) and KOSEF (R-01-2004-000-10792-0).

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